

SEMICONDUCTOR PRODUCT

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C.B.C

TYPE	NPN Epitaxial Planar					
MATERIAL	Silicon					
APPLICATION	High Frequency Power Amplifier for 270MHz Band AM/SSB Transceiver					
OUTLINE	See Fig 1					
CONNECTION	See Fig 1					
ABSOLUTE MAXIMUM RATINGS	VCBO (V)	VCE ^{*1} (V)	VBE (V)	I _C ^{*2} (A)	P _C (W)	T _j (°C)
	70	70	4.0	8	25	150
	-55 ~ +150					
	Ta = 25°C					

TEST SPECIFICATION

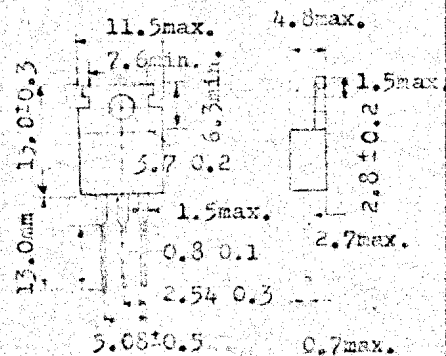
Ta = 25°C

Symbol	Condition	Typ.	Limit		Unit
			Min	Max	
ICBO	VCE=40V, IE=0			20	μA
hFE	VCE=10V, IC=2.0A		20	150	
VCE(sat)	IC=2.0A, IE=0.4A	0.2		0.5	V
fT	VCE=10V, IC=0.5A	150			MHz
Cob	VCE=10V, f=1MHz, IE=0	80			PF
Po	VCC=12V, f=50MHz, Pi=3W		13.0		W
ηc	VCC=12V, f=50MHz, Pi=3W		60		%

*1 RBE=100Ω

Fig 1

*2 PW=20mS, Duty Cycle 50%



BCE

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